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Kind regards,

Team Nexperia



PMBTA42

300 V, 100 mA NPN high-voltage transistor Rev. 05 — 12 December 2008

Product data sheet

Product profile

1.1 General description

NPN high-voltage transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

PNP complement: PMBTA92.

1.2 Features

■ High voltage (max. 300 V)

1.3 Applications

Telephony and professional communication equipment

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	300	V
I _C	collector current		-	-	100	mA
h _{FE}	DC current gain	$V_{CE} = 10 \text{ V}$				
		$I_C = 1 \text{ mA}$	25	-	-	
		$I_C = 10 \text{ mA}$	40	-	-	
		$I_C = 30 \text{ mA}$	40	-	-	

Pinning information 2.

Table 2. **Pinning**

Pin	Description	Simplified outline	Graphic symbol
1	base		
2	emitter	3	3
3	collector	1 2	1 — 2
			sym021



300 V, 100 mA NPN high-voltage transistor

3. Ordering information

Table 3. Ordering information

Type number[1]	Package					
	Name	Description	Version			
PMBTA42	-	plastic surface-mounted package; 3 leads	SOT23			
PMBTA42/DG	_					

^{[1] /}DG: halogen-free

4. Marking

Table 4. Marking codes

Type number ^[1]	Marking code ^[2]
PMBTA42	*1D
PMBTA42/DG	*BV

^{[1] /}DG: halogen-free

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	300	V
V_{CEO}	collector-emitter voltage	open base	-	300	V
V_{EBO}	emitter-base voltage	open collector	-	6	V
Ic	collector current		-	100	mA
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	200	mA
I _{BM}	peak base current	single pulse; $t_p \le 1 \text{ ms}$	-	100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u> -	250	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T_{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

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^{[2] * = -:} made in Hong Kong

^{* =} p: made in Hong Kong

^{* =} t: made in Malaysia

^{* =} W: made in China

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300 V, 100 mA NPN high-voltage transistor

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Thermal characteristics

Table 6. **Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1] -	-	500	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

Characteristics 7.

Product data sheet

Characteristics Table 7.

 $T_{amb} = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I_{CBO}	collector-base cut-off current	$V_{CB} = 200 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 6 \text{ V}; I_C = 0 \text{ A}$	-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 10 V				
		I _C = 1 mA	25	-	-	
		$I_C = 10 \text{ mA}$	40	-	-	
		$I_C = 30 \text{ mA}$	40	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 20 \text{ mA}; I_B = 2 \text{ mA}$	-	-	500	mV
V _{BEsat}	base-emitter saturation voltage	$I_C = 20 \text{ mA}; I_B = 2 \text{ mA}$	-	-	900	mV
C _{re}	feedback capacitance	$V_{CB} = 20 \text{ V}; I_C = I_c = 0 \text{ A};$ f = 1 MHz	-	-	3	pF
f _T	transition frequency	$V_{CE} = 20 \text{ V}; I_{C} = 10 \text{ mA};$ f = 100 MHz	50	-	-	MHz

EUROPEAN

PROJECTION

ISSUE DATE

04-11-04

06-03-16

8. Package outline

Plastic surface-mounted package; 3 leads

SOT23

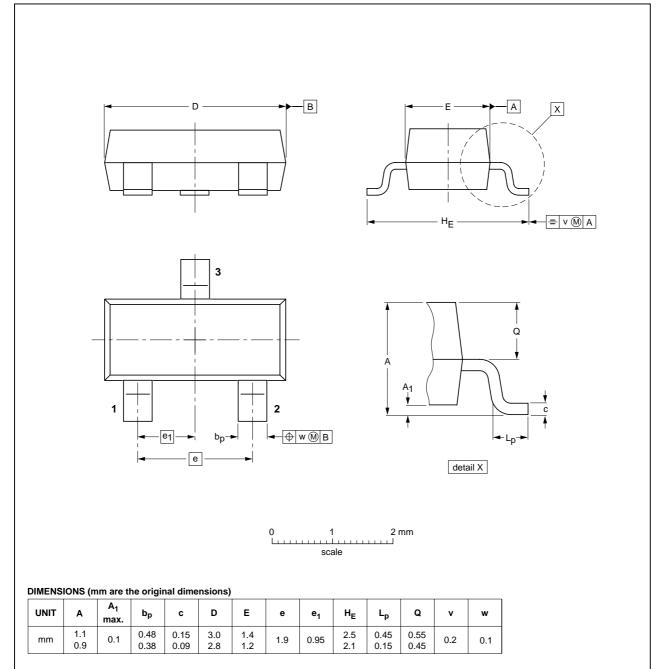


Fig 1. Package outline SOT23 (TO-236AB)

IEC

OUTLINE

VERSION

SOT23

JEITA

REFERENCES

JEDEC

TO-236AB

PMBTA42 **NXP Semiconductors**

300 V, 100 mA NPN high-voltage transistor

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Packing information 9.

Table 8. **Packing methods**

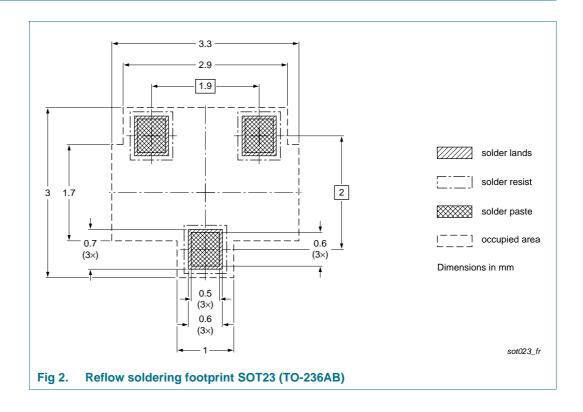
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity	
			3000	10000
PMBTA42	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235
PMBTA42/DG				

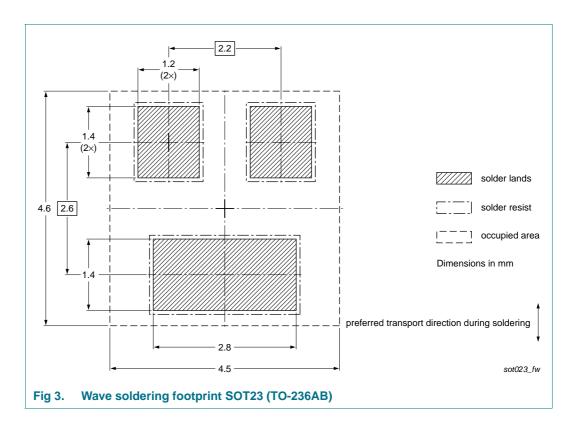
- [1] For further information and the availability of packing methods, see Section 13.
- [2] /DG: halogen-free

10. Soldering

Product data sheet



300 V, 100 mA NPN high-voltage transistor



300 V, 100 mA NPN high-voltage transistor

11. Revision history

Table 9. Revision history

	•			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PMBTA42_5	20081212	Product data sheet	-	PMBTA42_4
Modifications:		t of this data sheet has been of NXP Semiconductors.	redesigned to comply v	with the new identity
	 Legal texts 	s have been adapted to the n	new company name who	ere appropriate.
	 Type num 	ber PMBTA42/DG added		
	 Table 4 "M 	larking codes": enhanced		
	 Section 12 	2 "Legal information": updated	d	
PMBTA42_4	20040122	Product specification	-	PMBTA42_3
PMBTA42_3	19990422	Product specification	-	PMBTA42_43_CNV_2

300 V, 100 mA NPN high-voltage transistor

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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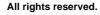
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